

SEMICONDUCTOR TM

KSD1408

Power Amplifier Applications

Complement to KSB1017



KSD1408

1.Base 2.Collector 3.Emitter

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	80	V
V _{CEO}	Collector-Emitter Voltage	80	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	4	Α
I _B	Base Current	0.4	А
P _C	Collector Dissipation (T _C =25°C)	25	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

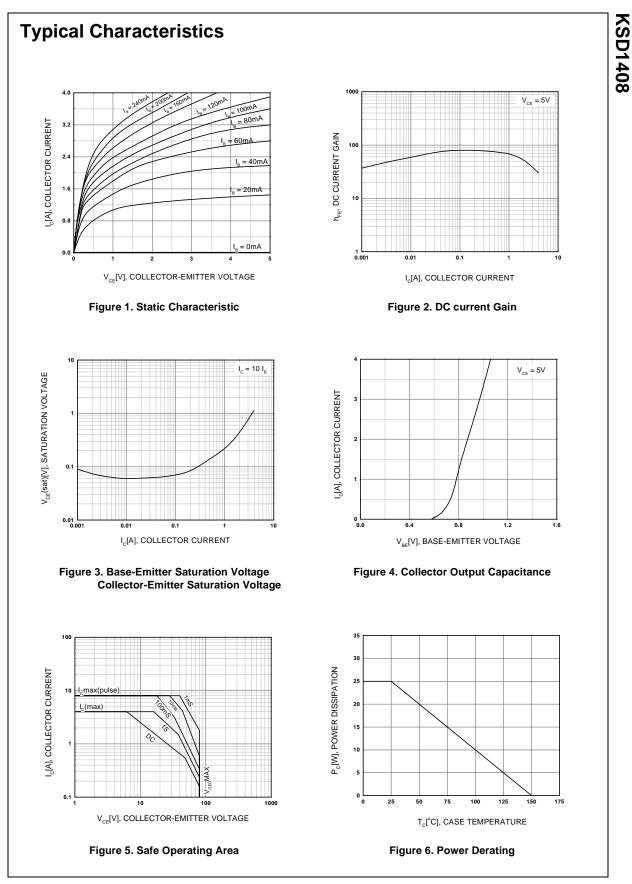
Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 50 {\rm mA}, I_{\rm B} = 0$	80			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 80V, I_E = 0$			30	μA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			100	μA
h _{FE1}	DC Current Gain	$V_{CE} = 5V, I_{C} = 0.5A$	40		240	
h _{FE2}		$V_{CE} = 5V, I_{C} = 3A$	15	50		
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = 3A. I _B = 0.3A		0.45	1.5	V
V _{BE} (on)	Base-Emitter On Voltage	$V_{CE} = 5V, I_{C} = 3A$		1	1.5	V
f _T	Current Gain Bandwidth Product	$V_{CE} = 5V, I_{C} = 0.5A$		8		MHz
C _{ob}	Output Capacitance	V _{CB} = 10V, f = 1MHz		90		pF

h_{FE1} Classification

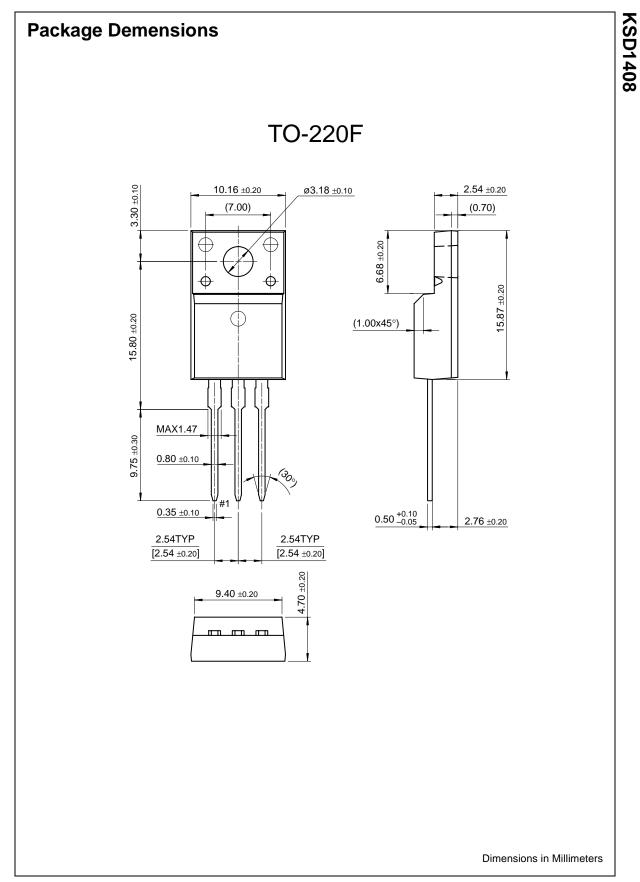
Classification	R	0	Y			
h _{FE1}	40 ~ 80	70 ~ 140	120 ~ 240			

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